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MOS FET

FL6L52070L

Panasonic

FL6L52070L

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

■ Features

- Low drain-source ON resistance : RDS (on) typ. = 300 m Ω (VGS = -4.0 V)
- Low drive voltage: 2.5 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol Y4

Established: 2011-05-16

: 2013-10-18

Revised

■ Packaging

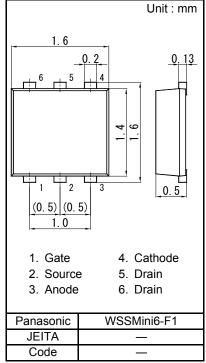
Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

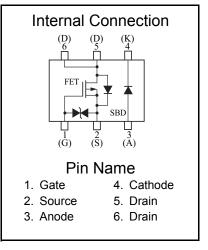
■ Absolute Maximum Ratings Ta = 25 °C

		Symbol	Rating	Unit	
FET	Drain to Source Voltage	VDS	-20	V	
	Gate to Source Voltage	VGS	±12	V	
	Drain current	ID	-1.0	Α	
	Peak drain current	IDp	-4.0	Α	
	Channel temperature	Tch	150	°C	
SBD	Reverse voltage	VR	20	V	
	Forward current (Average)	IF(AV)	700	mA	
	Junction temperature	Tj	125	°C	
Overall	Total power dissipation *1	PD	540	mW	
	Operating ambient temperature	Topr	-40 to +85	°C	
	Storage temperature	Tstg	-55 to +125	°C	

Note: *1 Glass epoxy board (25.4 x 25.4 x t0.8 mm) coated with copper foil, which has more than 300mm².

PD absolute maximum rating without a heat shink: 150 mW





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■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDSS	ID = -1.0 mA, VGS = 0 V	-20			V
Drain-source cutoff current	IDSS	VDS = -20 V, VGS = 0 V			-1.0	μΑ
Gate-source cutoff current	IGSS	VGS = ±10 V, VDS = 0 V			±10	μA
Gate threshold voltage	VTH	ID = -1.0 mA, VDS = -10 V	-0.45	-1.0	-1.5	V
Drain-source ON resistance *1	RDS(on)1	ID = -0.5 A, VGS = -4.0 V		300	420	mΩ
Drain-source On resistance	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		420	560	
Forward transfer admittance *1	Yfs	ID = -0.5 A, VDS = -10 V, f = 1 kHz	1.0			S
Short-circuit input capacitance (Common source)	Ciss			80		
Short-circuit output capacitance (Common source)	Coss	VDS = -10 V, VGS = 0 V, f = 1 MHz		12		pF
Reverse transfer capacitance (Common source)	Crss			12		
Turn-on delay time *2	td(on)	VDD = -15 V, VGS = 0 to - 4.0 V		12		no
Rise time *2	tr	ID = -0.5 A		6		ns
Turn-off delay time *2	td(off)	VDD = -15 V, VGS = - 4.0 to 0 V		17		no
Fall time *2	tf	ID = -0.5 A		10		ns

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Forward voltage	VF1	IF = 10 mA			0.4	\ <u>'</u>	
Forward voltage	VF2	IF = 500 mA			0.55	V	
Reverse current	IR1	VR = 5 V			1		
Neverse current	IR2	VR = 10 V			10	μΑ	

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

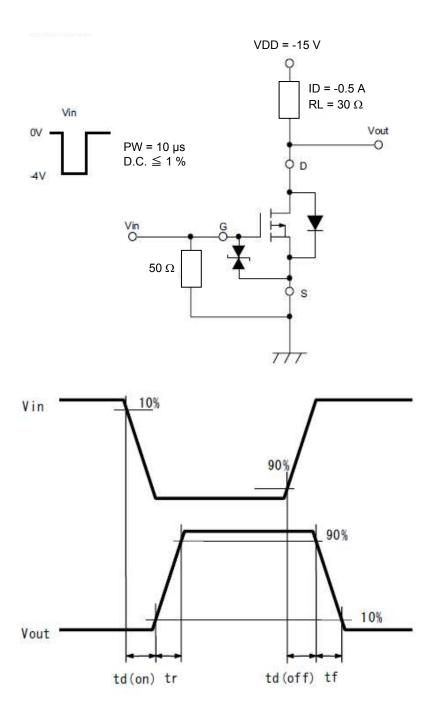
^{2. *1} Pulse measurement

^{*2} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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MOS FET FL6L52070L

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

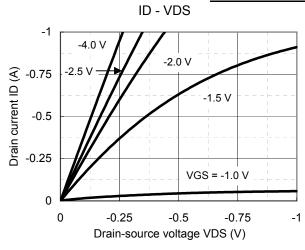


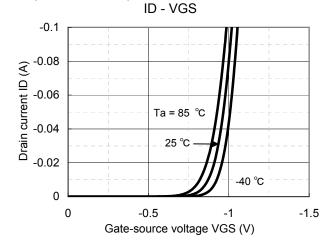
MOS FET

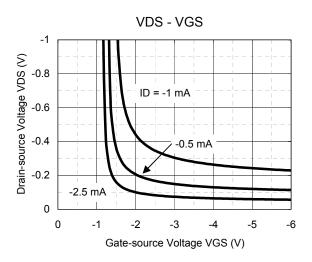
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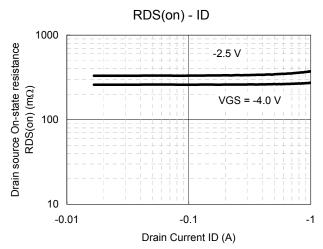
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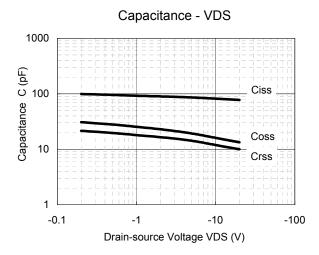
Technical Data (reference)

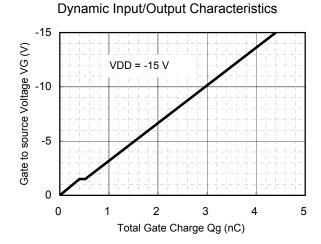










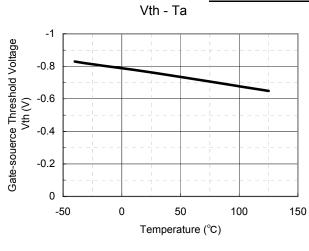


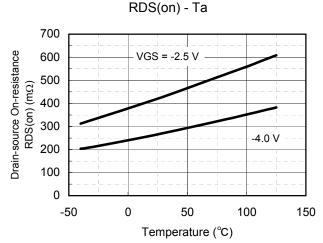
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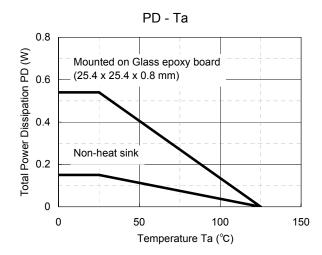
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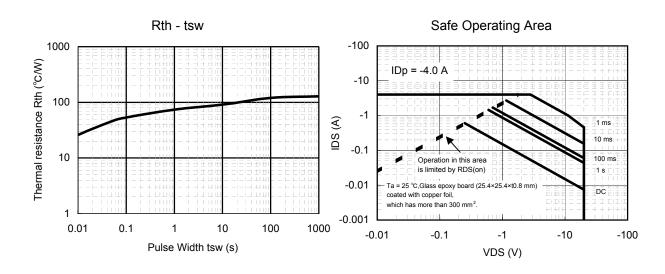
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Technical Data (reference)









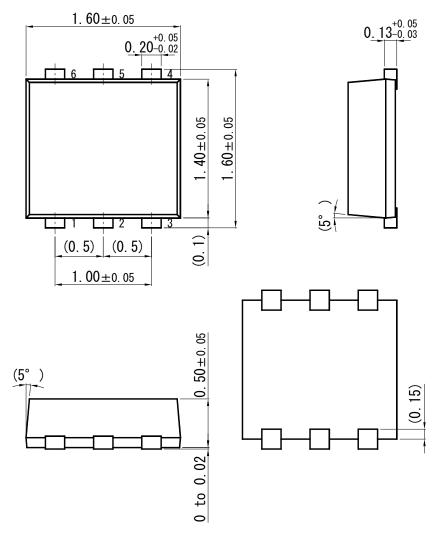
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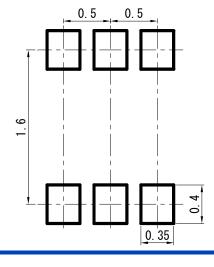
Panasonic

WSSMini6-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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